FAIRCHILD SEMICONDUCTOR®

November 2009

FDY4000CZ

Complementary N & P-Channel PowerTrench® MOSFET

Features

Q1: N-Channel

- Max $r_{DS(on)}$ = 0.7Ω at V_{GS} = 4.5V, I_D = 600mA
- Max $r_{DS(on)}$ = 0.85Ω at V_{GS} = 2.5V, I_D = 500mA
- Max $r_{DS(on)}$ = 1.25Ω at V_{GS} = 1.8V, I_D =150 mA

Q2: P-Channel

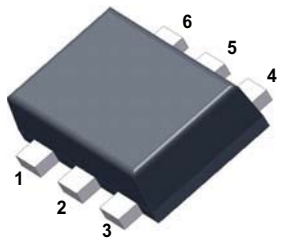
- Max $r_{DS(on)}$ = 1.2Ω at V_{GS} = -4.5V, I_D = -350mA
- Max $r_{DS(on)}$ = 1.6Ω at V_{GS} = -2.5V, I_D = -300mA
- Max $r_{DS(on)}$ = 2.7Ω at V_{GS} = -1.8V, I_D = -150mA
- ESD protection diode (note 3)
- RoHS Compliant

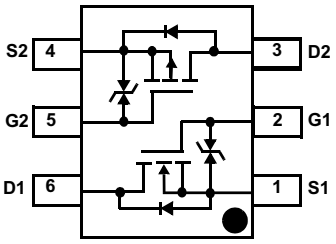
General Description

This Complementary N & P-Channel MOSFET has been designed using Fairchild Semiconductor's advanced Power Trench® process to optimize the $r_{DS(ON)}$ @ V_{GS}= 2.5V and specify the $r_{DS(ON)}$ @ V_{GS} = 1.8V.

Applications

- Level shifting
- Power Supply Converter Circuits
- Load/Power Switching Cell Phones, Pagers





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter		Q1	Q2	Units
V_{DS}	Drain to Source Voltage		20	-20	V
V_{GS}	Gate to Source Voltage		±12	±8	V
I_D	Drain Current -Continuous	(Note 1a)	600	-350	mA
	-Pulsed		1000	-1000	
P_D	Power Dissipation (Steady State)	(Note 1a)	625		mW
		(Note 1b)	446		
T_J, T_{STG}	Operating and Storage Jaunting Temperature Range		-55 to 150		°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	200	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1b)	280	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
E	FDY4000CZ	SC89-6	7"	8mm	3000units

Electrical Characteristics T_J = 25°C unless otherwise noted

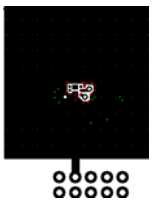
Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
Off Characteristics							
B_{VDSS}	Drain to Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V I_D = -250μA, V_{GS} = 0V	Q1 Q2	20 -20			V
$\frac{\Delta B_{VDSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250μA, referenced to 25°C I_D = -250μA, referenced to 25°C	Q1 Q2		15 -15		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 16V, V_{DS} =0V V_{DS} = -16V, V_{DS} =0V	Q1 Q2			1 -3	μA
I_{GSS}	Gate-Body Leakage	V_{GS} = ±12V, V_{DS} = 0V V_{GS} = ±4.5V, V_{DS} = 0V V_{GS} = ±8V, V_{DS} = 0V	Q1 Q1 Q2			±10 ±1 ±10	μA
On Characteristics (note 2)							
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250μA V_{GS} = V_{DS}, I_D = -250μA	Q1 Q2	0.6 -0.6	1.0 -1.0	1.5 -1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250μA, referenced to 25°C I_D = -250μA, referenced to 25°C	Q1 Q2		-3 3		mV/°C
$r_{DS(on)}$	Drain to Source On Resistance	V_{GS} = 4.5V, I_D = 600mA V_{GS} = 2.5V, I_D = 500mA V_{GS} = 1.8V, I_D = 150mA, V_{GS} = 4.5V, I_D = 600mA,T_J = 125°C	Q1		0.30 0.40 0.80 0.35	0.70 0.85 1.25 1.00	Ω
		V_{GS} = -4.5V, I_D = --350mA V_{GS} = -2.5V, I_D = -300mA V_{GS} = -1.8V, I_D = -150mA V_{GS} = -4.5V, I_D = -350mA, T_J =125°C	Q2		0.5 0.8 1.3 0.7	1.2 1.6 2.7 1.6	
g_{FS}	Forward Transconductance	V_{DS} = 5V, I_D = 600mA V_{DS} = -5V, I_D = -350mA	Q1 Q2		1.8 1		S
Dynamic Characteristics							
C_{iss}	Input Capacitance	Q1 V_{DS} = 10V, V_{GS} = 0V, f = 1MHz Q2 V_{DS} = -10V, V_{GS} = 0V, f = 1MHz	Q1 Q2		60 100		pF
C_{oss}	Output Capacitance		Q1 Q2		20 30		pF
C_{rss}	Reverse Transfer Capacitance		Q1 Q2		10 15		pF
Switching Characteristics							
$t_{d(on)}$	Turn-On Delay Time	Q1 V_{DD}= 10V, I_D = 1A, V_{GS}= 4.5V, R_g = 6Ω Q2 V_{DD}= -10V, I_D = -0.5A, V_{GS}= -4.5V, R_g = 6Ω	Q1 Q2		6 6	12 12	ns
t_r	Rise Time		Q1 Q2		8 13	16 23	ns
$t_{d(off)}$	Turn-Off Delay Time		Q1 Q2		8 8	16 16	ns
t_f	Fall Time		Q1 Q2		2.4 1	4.8 2	ns
Q_g	Total Gate Charge	Q1 V_{DS}= 10V, I_D = 600mA, V_{GS}= 4.5V Q2 V_{DS}= -10V, I_D = -350mA, V_{GS}= -4.5V	Q1 Q2		0.8 1.0	1.1 1.4	nC
Q_{gs}	Gate to Source Gate Charge		Q1 Q2		0.16 0.2		nC
Q_{gd}	Gate to Drain “Miller”Charge		Q1 Q2		0.26 0.3		nC

Electrical Characteristics T_J = 25°C unless otherwise noted

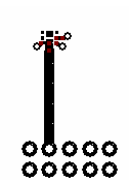
Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
Drain-Source Diode Characteristics							
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0V, I_S = 150mA (Note 2) V_{GS} = 0V, I_S = -150mA (Note 2)	Q1 Q2		0.7 -0.8	1.2 -1.2	V
t_{rr}	Reverse Recovery Time	Q1 I_F = 600mA, di/dt = 100A/µs	Q1 Q2		8 11		ns
Q_{rr}	Reverse Recovery Charge	Q2 I_F = -350mA, di/dt = 100A/µs	Q1 Q2		1 2		nC

Notes:

1: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design.



a) 200°C/W when mounted on a 1 in^2 pad of 2 oz copper



b) 280°C/W when mounted on a minimum pad of 2 oz copper

Scale 1:1 on letter size paper

2: Pulse Test : Pulse Width < 300us, Duty Cycle < 2.0%

3: The diode connected between the gate and source serves only as protection against ESD. No gate overvoltage rating is implied.

Typical Characteristics Q1 (N-Channel)

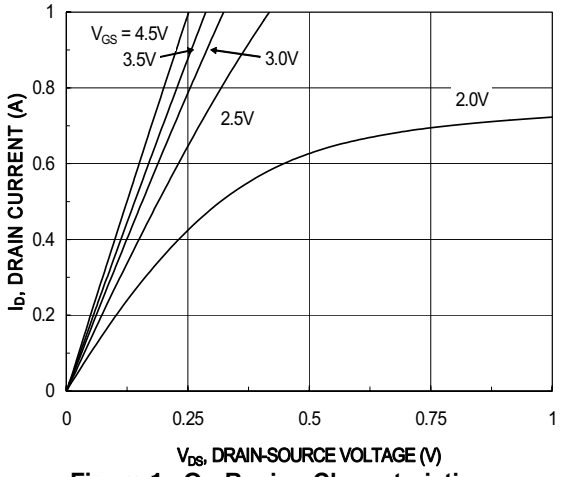


Figure 1. On-Region Characteristics

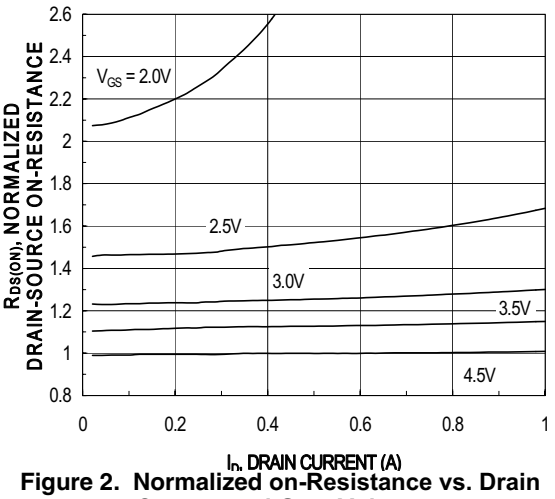


Figure 2. Normalized on-Resistance vs. Drain Current and Gate Voltage

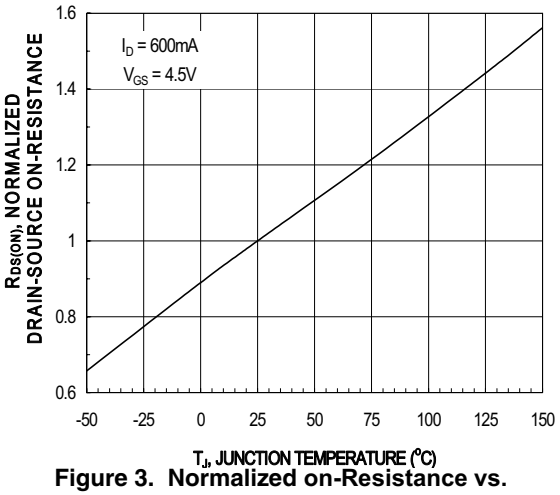


Figure 3. Normalized on-Resistance vs. Temperature

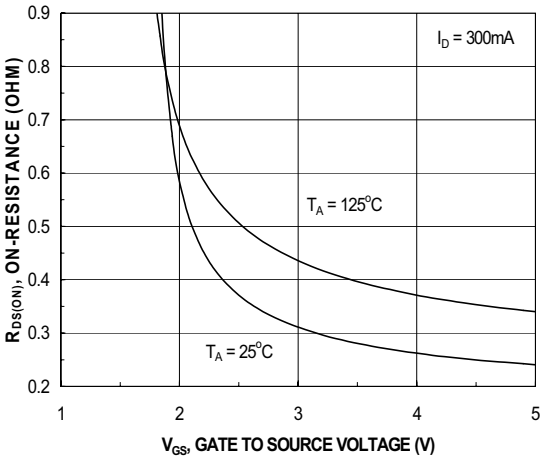


Figure 4. On-Resistance vs. Gate-to-Source Voltage

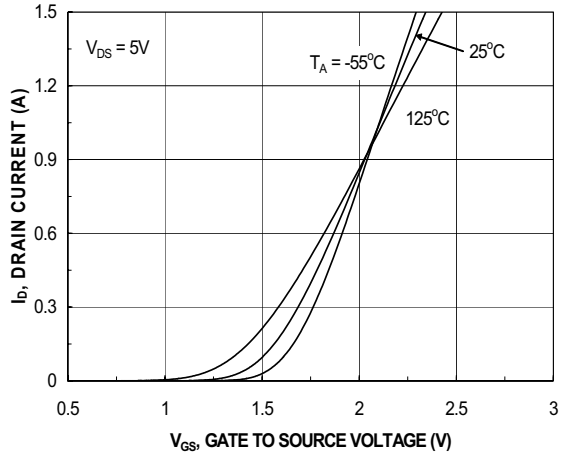


Figure 5. Transfer Characteristics

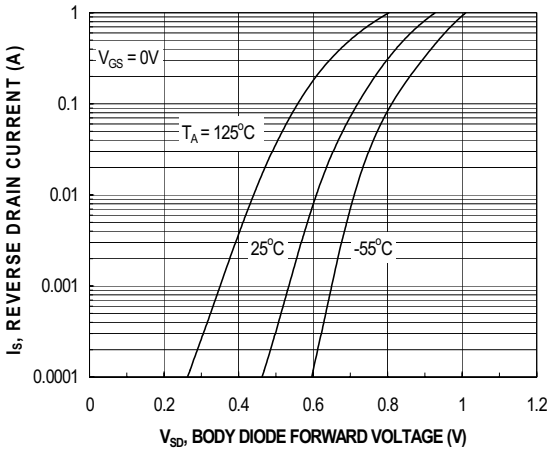


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current and Temperature

Typical Characteristics Q1 (N-Channel)

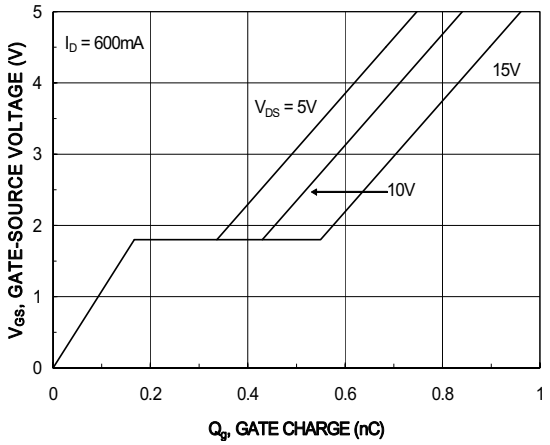


Figure 7. Gate Charge Characteristics

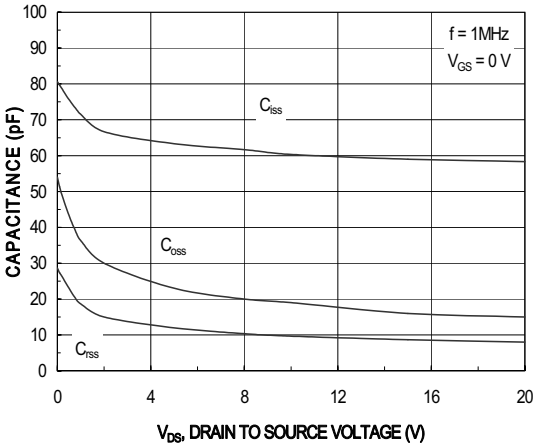


Figure 8. Capacitance vs. Drain to source voltage

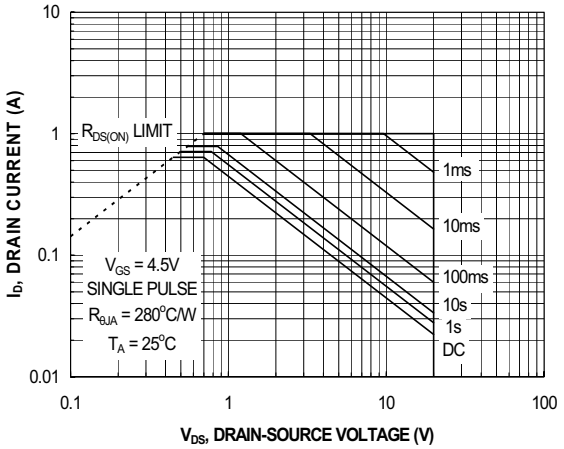


Figure 9. Maximum Safe Operating Area

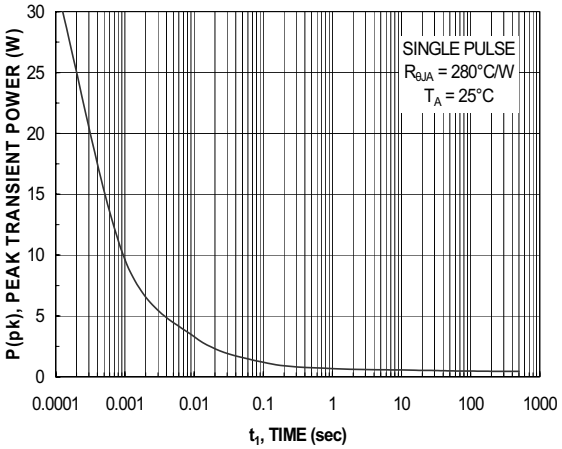


Figure 10. Single Pulse Maximum Power Dissipation

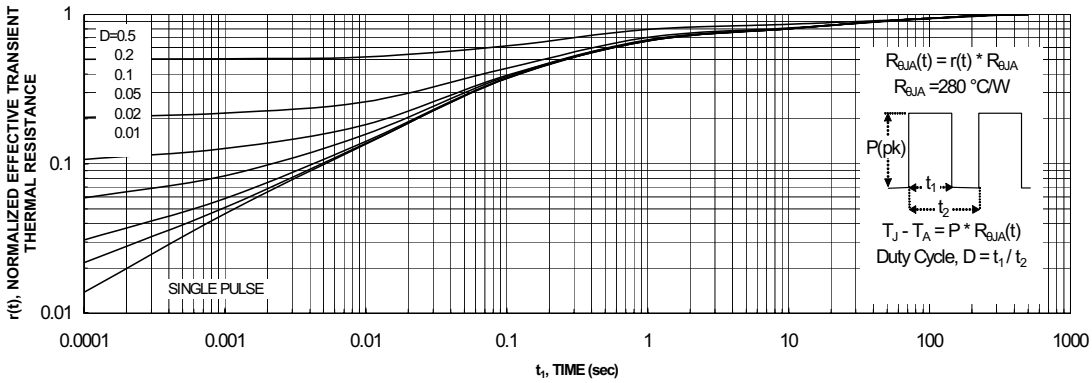


Figure 11. Transient Thermal Response Curve

Thermal characterization performed using the conditions described in Note 1b. Transient thermal response will change depending on the circuit board design.

Typical Characteristics Q2 (P-Channel)

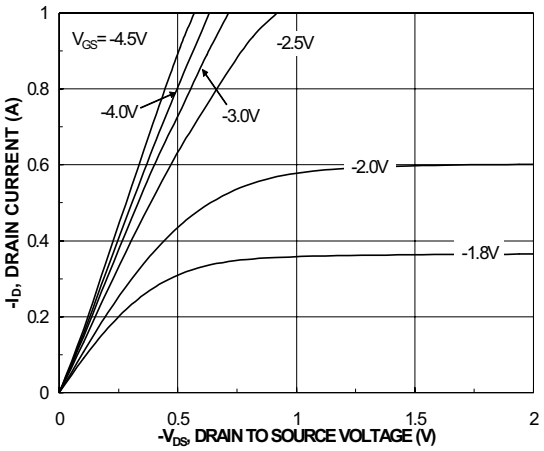


Figure 12. On-Region Characteristics

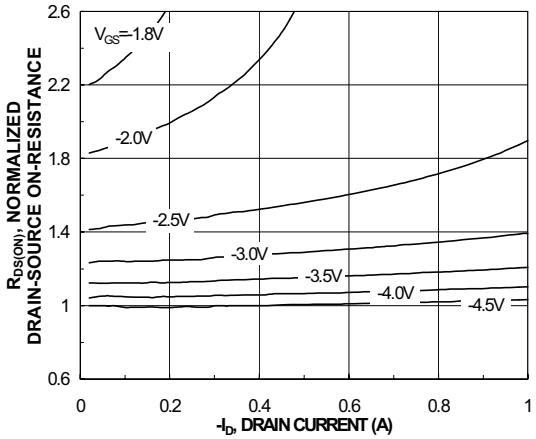


Figure 13. Normalized on-Resistance vs. Drain Current and Gate Voltage

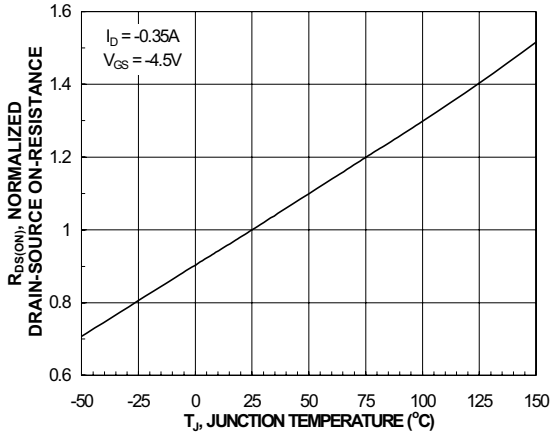


Figure 14. Normalized on-Resistance vs. Temperature

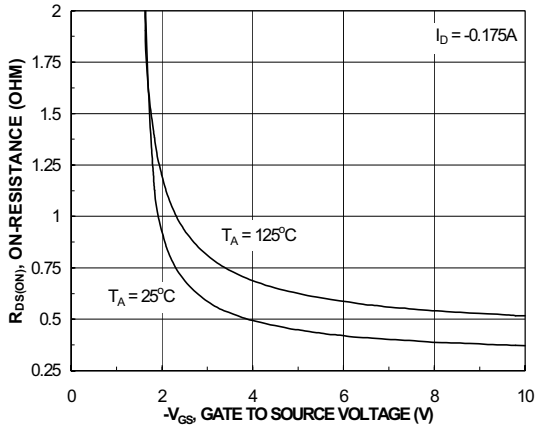


Figure 15. On-Resistance vs. Gate-to-Source Voltage

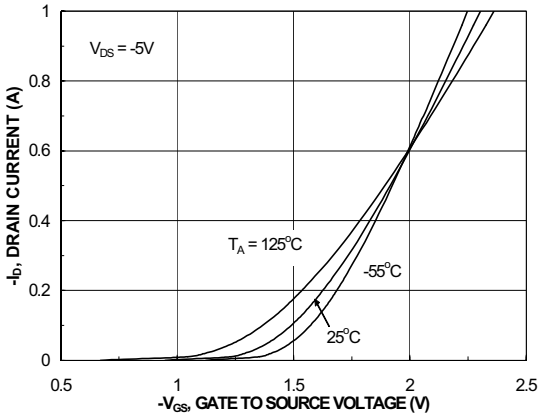


Figure 16. Transfer Characteristics

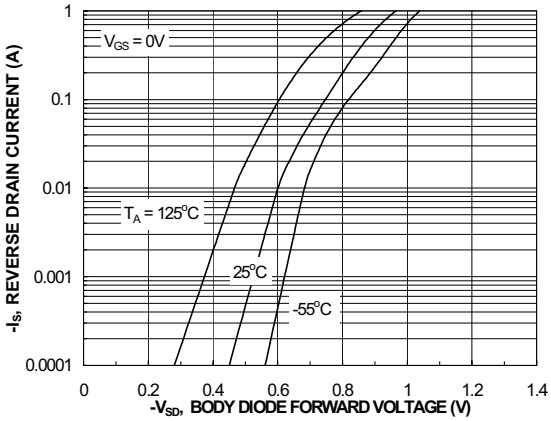


Figure 17. Source to Drain Diode Forward Voltage vs. Source Current and Temperature

Typical Characteristics Q2 (P-Channel)

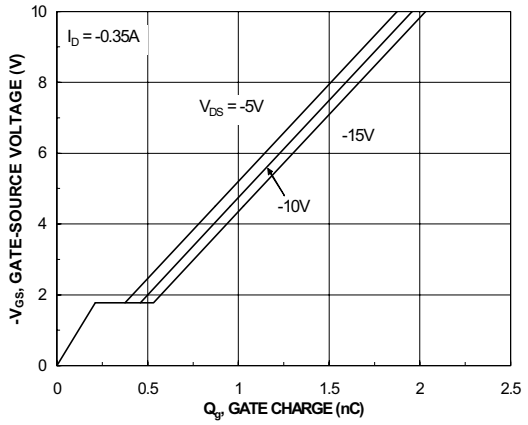


Figure 18. Gate Charge Characteristics

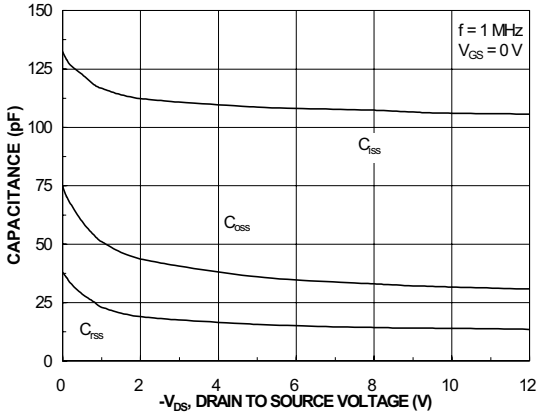


Figure 19. Capacitance vs. Drain to source voltage

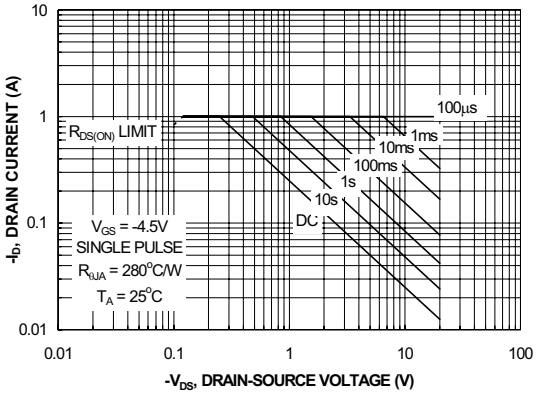


Figure 20. Maximum Safe Operating Area

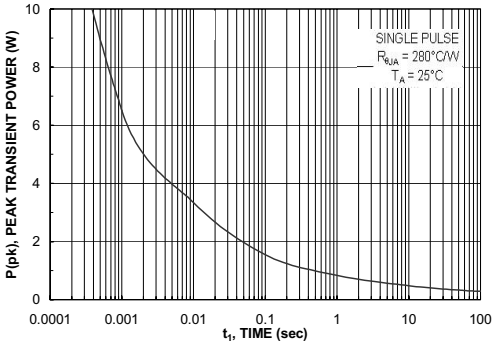


Figure 21. Single Pulse Maximum Power Dissipation

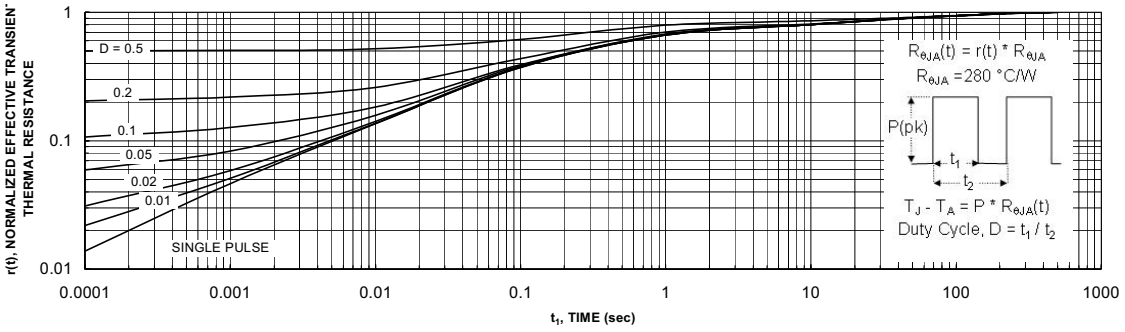
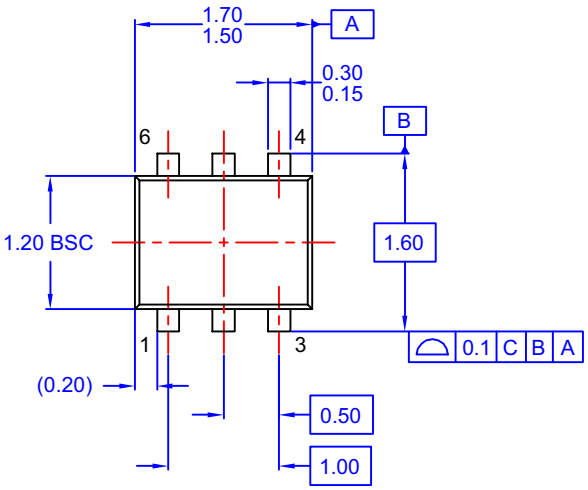


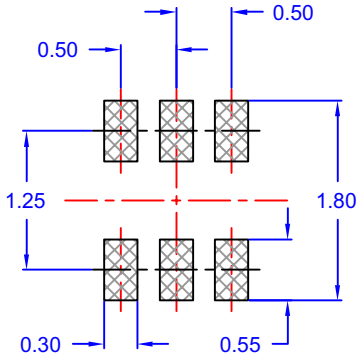
Figure 22. Transient Thermal Response Curve

Thermal characterization performed using the conditions described in Note 1b.
Transient thermal response will change depending on the circuit board design.

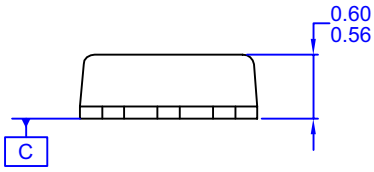
Dimensional Outline and Pad Layout

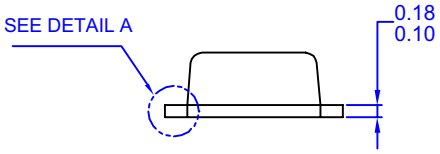


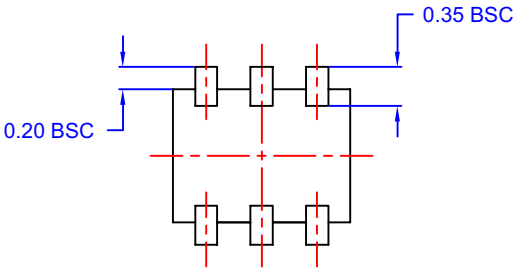
TOP VIEW



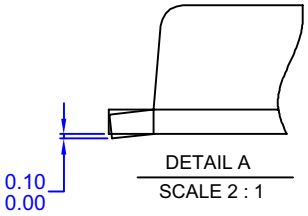
LAND PATTERN RECOMMENDATION







BOTTOM VIEW



DETAIL A
SCALE 2 : 1

NOTES:

A) THIS PACKAGE CONFORMS TO EIAJ SC89 PACKAGING STANDARD.
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DRAWING CONFORMS TO ASME Y14.5M-1994
D) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.

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Fairchild®
Fairchild Semiconductor®
FACT Quiet Series™
FACT®
FAST®
FastvCore™
FETBench™
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Green FPS™ e-Series™
G*max*™
GTO™
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MegaBuck™
MICROCOUPLER™
MicroFET™
MicroPak™
MillerDrive™
MotionMax™
Motion-SPM™
OPTOLOGIC®
OPTOPLANAR®
®
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PowerTrench®
PowerXS™
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SuperSOT™-8
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the power franchise®
TinyBoost™
TinyBuck™
TinyCalc™
TinyLogic®
TINYOPTO™
TinyPower™
TinyPWM™
TinyWire™
TriFault Detect™
TRUECURRENT™*
SerDes
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Ultra FRFET™
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VCX™
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2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.Fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handing and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

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